PD - 95264B

International
IOR Rectifier

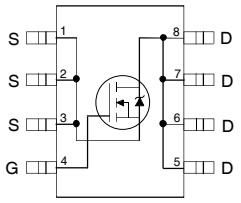
IRF7811APbF

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	Q_g
28V	12mΩ	17nC

Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- 100% R_G Tested
- Lead-Free



Top View


SO-8

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current

Absolute Maximum Ratings

Symbol	Parameter	Max	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	11④	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	9.1 ④	
I_{DM}	Pulsed Drain Current ①	91	
P_D @T_A = 25°C	Power Dissipation ④	2.5	W
P_D @T_A = 70°C	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	±12	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Smoldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

Symbol	Parameter	Typ	Max	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	–––	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④⑤	–––	50	

Notes ① through ⑤ are on page 10

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	28	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.025	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	8.7	10	mΩ	V_{GS} = 10V, I_D = 11A ④
		—	10	12		V_{GS} = 4.5V, I_D = 9.0A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-4.0	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	12	µA	V_{DS} = 28V, V_{GS} = 0V
		—	—	150		V_{DS} = 24V, V_{GS} = 0V, T_J = 100°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -12V
g_{fs}	Forward Transconductance	28	—	—	S	V_{DS} = 15V, I_D = 9.0A
Q_g	Total Gate Charge	—	17	26	nC	V_{DS} = 15V V_{GS} = 4.5V I_D = 9.0A See Fig. 16
Q_{gs1}	Pre-Vth Gate-Source Charge	—	3.3	—		
Q_{gs2}	Post-Vth Gate-Source Charge	—	1.3	—		
Q_{gd}	Gate-to-Drain Charge	—	4.7	—		
Q_{godr}	Gate Charge Overdrive	—	7.2	—		
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	6.0	—		
Q_{oss}	Output Charge	—	24	—	nC	V_{DS} = 16V, V_{GS} = 0V
R_G	Gate Resistance	0.9	—	3.7	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	7.5	—	ns	V_{DD} = 15V, V_{GS} = 4.5V ④ I_D = 9.0A Clamped Inductive Load
t_r	Rise Time	—	4.1	—		
$t_{d(off)}$	Turn-Off Delay Time	—	19	—		
t_f	Fall Time	—	6.5	—		
C_{iss}	Input Capacitance	—	1760	—	pF	V_{GS} = 0V V_{DS} = 15V f = 1.0MHz
C_{oss}	Output Capacitance	—	960	—		
C_{rss}	Reverse Transfer Capacitance	—	54	—		

Avalanche Characteristics

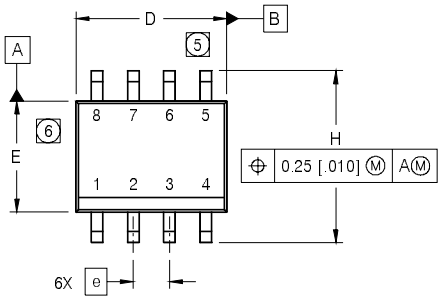
Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	58	mJ
I_{AR}	Avalanche Current ①	—	9.0	A

Diode Characteristics

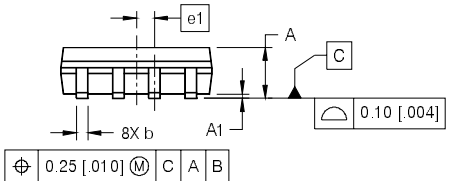
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	11	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	91		
V_{SD}	Diode Forward Voltage	—	0.8	1.0	V	T_J = 25°C, I_S = 9.0A, V_{GS} = 0V③
		—	0.66	—		T_J = 125°C, I_S = 9.0A, V_{GS} = 0V③
t_{rr}	Reverse Recovery Time	—	72	110	ns	T_J = 25°C, I_F = 9.0A, V_R = 15V di/dt = 100A/µs ③
Q_{rr}	Reverse Recovery Charge	—	93	140	nC	
t_{rr}	Reverse Recovery Time	—	73	110	ns	T_J = 125°C, I_F = 9.0A, V_R = 15V di/dt = 100A/µs ③
Q_{rr}	Reverse Recovery Charge	—	100	150	nC	

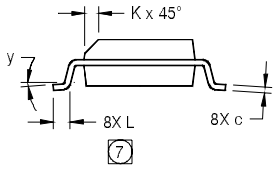
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



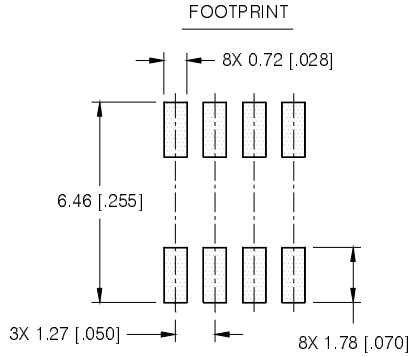
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°





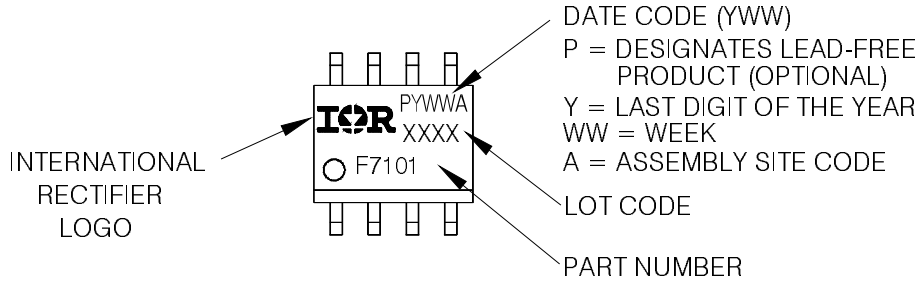
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



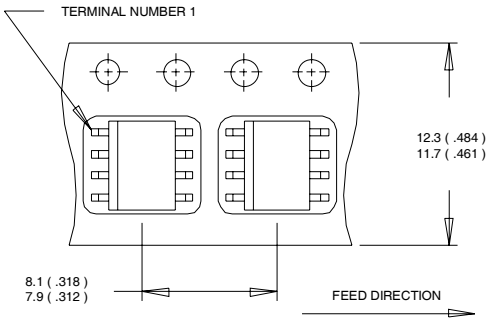
SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

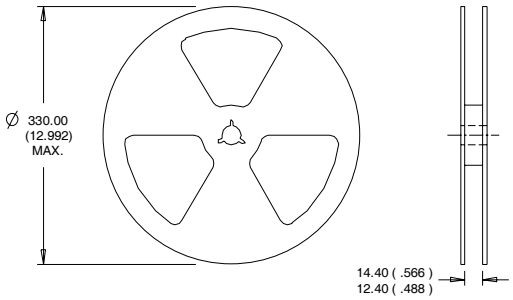


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 1.4mH R_G = 25Ω, I_{AS} = 9.0A.

③ Pulse width ≤ 300µs; duty cycle ≤ 2%.

④ When mounted on 1 inch square copper board

⑤ R_θ is measured at T_J approximately at 90°C

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.

International
IOR Rectifier